



迈拓电子
MAITUO ELECTRONIC

PBSS5160T

Descriptions

Silicon PNP transistor in a SOT-23 Plastic Package.

Features

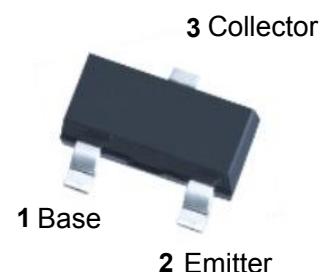
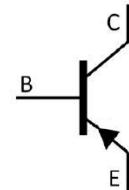
Low $V_{CE(sat)}$, high current.

Applications

General purpose switching and muting

LCD back-lighting

Supply line switching circuits.



SOT23

h_{FE} Classifications & Marking

h_{FE} Range	>150
Marking	HU6



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Absolute Maximum Ratings(Ta=25 °C)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V _{CBO}	-80	V
Collector to Emitter Voltage	V _{CEO}	-60	V
Emitter to Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-1	A
Peak Collector Current	I _{CM}	-2	A
Base Current	I _B	-0.3	A
Peak Base Current	I _{BM}	-1	A
Total Power Dissipation	P _C	400	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

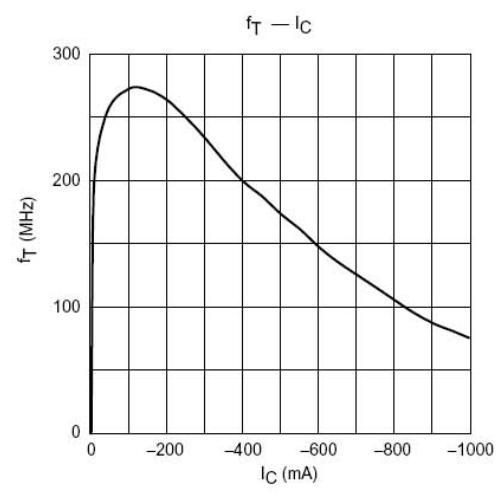
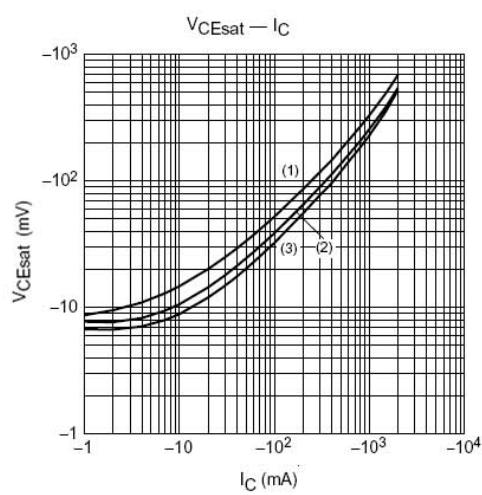
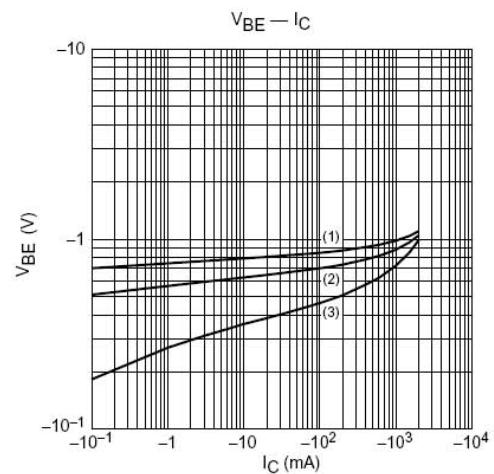
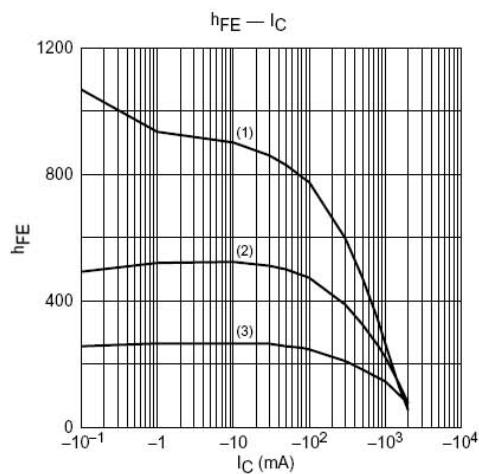
Electrical Characteristics(Ta=25 °C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I _{CBO}	V _{CB} =-60V I _E =0A			-100	nA
		V _{CB} =-60V I _E =0A T _j =150°C			-50	μA
Collector-Emitter Cut-Off Current	I _{CES}	V _{CE} =-60V V _{BE} =0V			-100	nA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-5V I _C =0A			-100	nA
DC Current Gain	h _{FE(1)}	V _{CE} =-5V I _C =-500mA	150	250		
	h _{FE(2)}	V _{CE} =-5V I _C =-1mA	200	350		
	h _{FE(3)}	V _{CE} =-5V I _C =-1A	100	160		
Collector-Emitter Saturation Voltage	V _{CE(sat)(1)}	I _C =-100mA I _B =-1mA		-110	-160	mV
	V _{CE(sat)(2)}	I _C =-500mA I _B =-50mA		-120	-175	mV
	V _{CE(sat)(3)}	I _C =-1A I _B =-100mA		-220	-330	mV
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-1A I _B =-50mA		-0.95	-1.1	V
Base-Emitter Voltage	V _{BE}	V _{CE} =-5V I _C =-1A		-0.82	-0.9	V
Transition Frequency	f _T	V _{CE} =-10V I _C =-50mA f=100MHz	150	220		MHz
Collector Capacitance	C _C	V _{CB} =-10V I _E =0A f=1MHz		9	15	pF



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Electrical Characteristic Curve





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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

